MOSFETs Silicon N-channel MOS (U-MOSVII-H)

# **TPN14006NH**

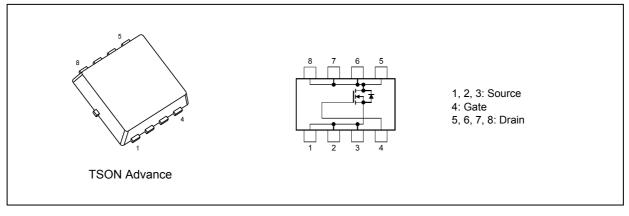
### 1. Applications

- Switching Voltage Regulators
- Motor Drivers
- DC-DC Converters

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 5.5 \text{ nC}$  (typ.)
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 11 \text{ m}\Omega$  (typ.)
- (4) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 60 \ V)$
- (5) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.2 mA)

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteris                   | Symbol                   | Rating             | Unit             |            |    |
|-------------------------------|--------------------------|--------------------|------------------|------------|----|
| Drain-source voltage          |                          |                    | V <sub>DSS</sub> | 60         | V  |
| Gate-source voltage           |                          |                    | V <sub>GSS</sub> | ±20        | V  |
| Drain current (DC)            | (Silicon limit)          | (Note 1), (Note 2) | Ι <sub>D</sub>   | 33         | A  |
| Drain current (DC)            |                          | (Note 1)           | Ι <sub>D</sub>   | 13         |    |
| Drain current (pulsed)        | (t = 1 ms)               | (Note 1)           | I <sub>DP</sub>  | 65         | A  |
| Power dissipation             | (T <sub>c</sub> = 25 °C) |                    | PD               | 30         | W  |
| Power dissipation             | (t = 10 s)               | (Note 3)           | PD               | 1.9        | W  |
| Power dissipation             | (t = 10 s)               | (Note 4)           | PD               | 0.7        | W  |
| Single-pulse avalanche energy |                          | (Note 5)           | E <sub>AS</sub>  | 43         | mJ |
| Avalanche current             |                          |                    | I <sub>AR</sub>  | 13         | A  |
| Channel temperature           |                          |                    | T <sub>ch</sub>  | 150        | °C |
| Storage temperature           |                          |                    | T <sub>stg</sub> | -55 to 150 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

#### 5. Thermal Characteristics

| Characteristics                       |                          |          | Symbol                | Max   | Unit |
|---------------------------------------|--------------------------|----------|-----------------------|-------|------|
| Channel-to-case thermal resistance    | (T <sub>c</sub> = 25 °C) |          | R <sub>th(ch-c)</sub> | 4.16  | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s)               | (Note 3) | R <sub>th(ch-a)</sub> | 65.7  |      |
| Channel-to-ambient thermal resistance | (t = 10 s)               | (Note 4) | R <sub>th(ch-a)</sub> | 178.1 |      |

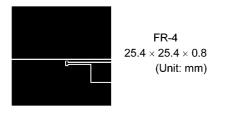
Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V\_DD = 48 V, T\_ch = 25 °C (initial), L = 0.2 mH, R\_G = 1  $\Omega,$  I\_AR = 13 A



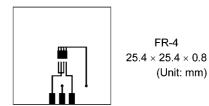


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a) Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

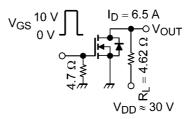
### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                         | Symbol               | Test Condition                                  | Min | Тур. | Max  | Unit |
|---|----------------------|---|-----|------|------|------|
| Gate leakage current                    | I <sub>GSS</sub>     | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V                | _   | _    | ±0.1 | μA   |
| Drain cut-off current                   | I <sub>DSS</sub>     | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V   | _   | _    | 10   |      |
| Drain-source breakdown voltage          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V   | 60  | _    | —    | V    |
| Drain-source breakdown voltage (Note 6) | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V | 45  | _    | —    |      |
| Gate threshold voltage                  | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.2 mA | 2.0 | _    | 4.0  |      |
| Drain-source on-resistance              | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 6.5 V, I <sub>D</sub> = 6.5 A | _   | 18   | 41   | mΩ   |
| Drain-source on-resistance              | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.5 A  |     | 11   | 14   | mΩ   |

Note 6: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition                             | Min | Тур. | Max  | Unit |
|--------------------------------|------------------|--|-----|------|------|------|
| Input capacitance              | C <sub>iss</sub> | $V_{DS}$ = 30 V, $V_{GS}$ = 0 V, f = 1 MHz | _   | 1000 | 1300 | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |  | —   | 25   | 55   | pF   |
| Output capacitance             | C <sub>oss</sub> |  | _   | 310  | _    | pF   |
| Gate resistance                | r <sub>g</sub>   | —  | _   | 2.0  | 3.0  | Ω    |
| Switching time (rise time)     | tr               | See Fig. 6.2.1                             | _   | 9    | —    | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | _   | 18   | _    | ns   |
| Switching time (fall time)     | t <sub>f</sub>   |  | _   | 5.5  | _    | ns   |
| Switching time (turn-off time) | t <sub>off</sub> |  | _   | 18   | _    | ns   |



 $Duty \le 1\%, \ t_w = 10 \ \mu s$  Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

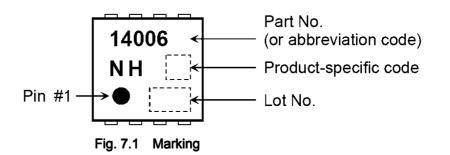
| Characteristics                                 | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx 30 \text{ V}, \text{ V}_{GS} \text{ = } 10 \text{ V}, \text{ I}_{D} \text{ = } 13 \text{ A}$ | _   | 15   | _   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |  | _   | 4.9  | _   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |  |     | 3.2  |     |      |
| Gate switch charge                              | Q <sub>SW</sub>  |  | _   | 5.5  |     |      |

### 6.4. Source-Drain Characteristics (Ta = 25 °C unless otherwise specified)

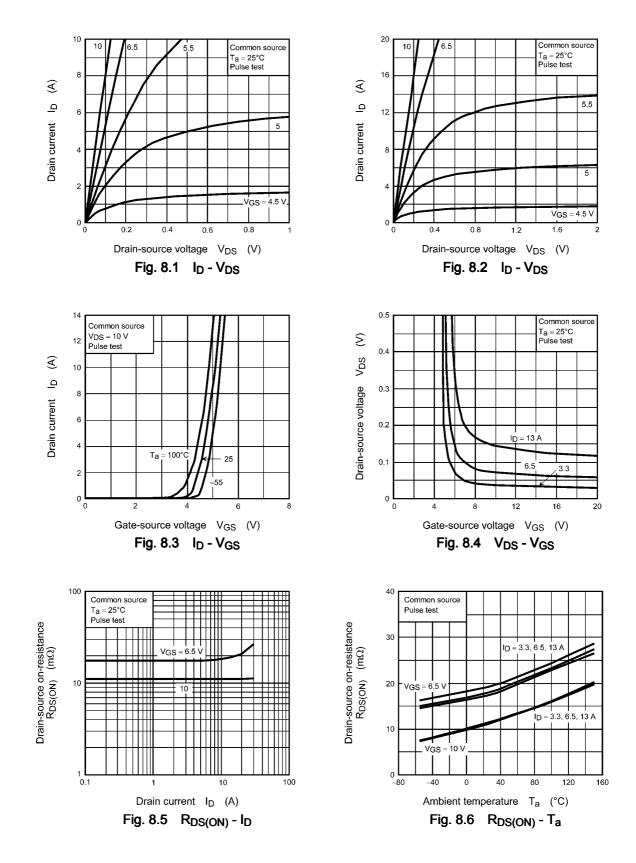
| Characteristics                |          | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|--------------------------------|----------|------------------|---|-----|------|------|------|
| Reverse drain current (pulsed) | (Note 7) | I <sub>DRP</sub> | —   | _   | —    | 65   | А    |
| Diode forward voltage          |          | V <sub>DSF</sub> | I <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V |     |      | -1.2 | V    |

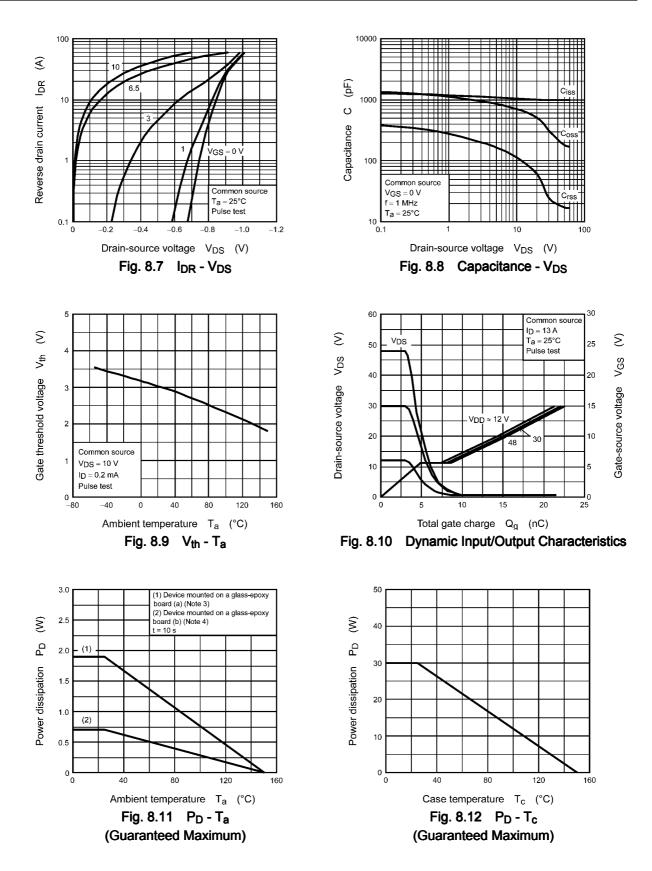
Note 7: Ensure that the channel temperature does not exceed 150 °C.

### 7. Marking

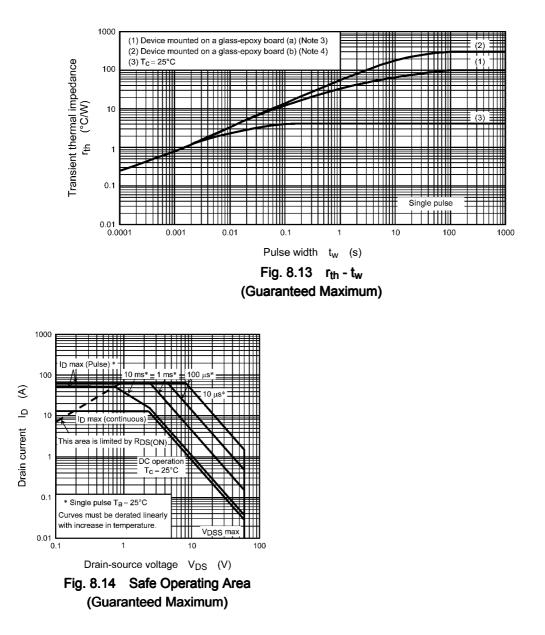


### 8. Characteristics Curves (Note)









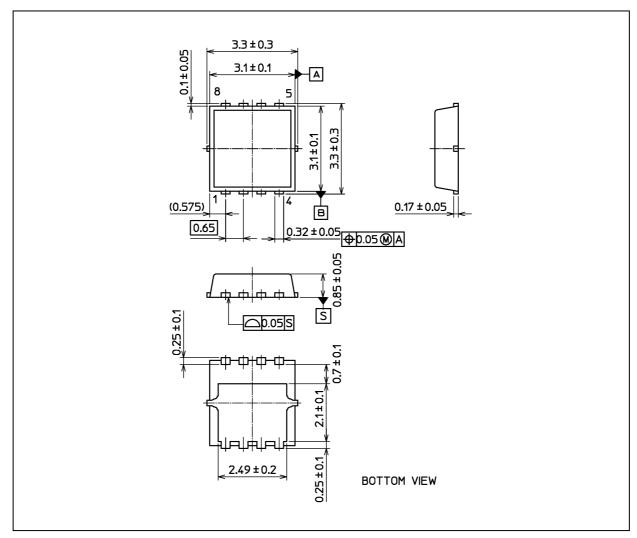
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### TPN14006NH

### **Package Dimensions**

Unit: mm



Weight: 0.02 g (typ.)

| Package Name(s)        |
|------------------------|
| TOSHIBA: 2-3X1S        |
| Nickname: TSON Advance |

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